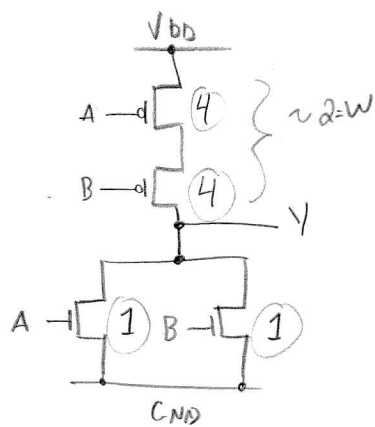
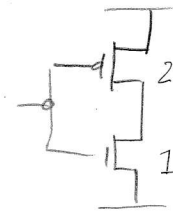


1-4.1)



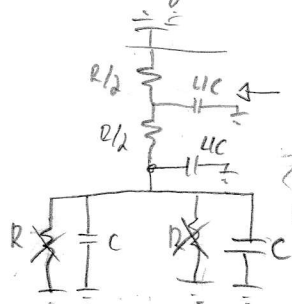
Same delay  
↔



\* Alternatively  
top PMOS's

$W=3$  for  $\frac{W_D}{W_N} = 1.5$

capacitance: if  $g=1$



Rising delay

$\frac{R}{2} \cdot 4C$   
 $6C$  self loading

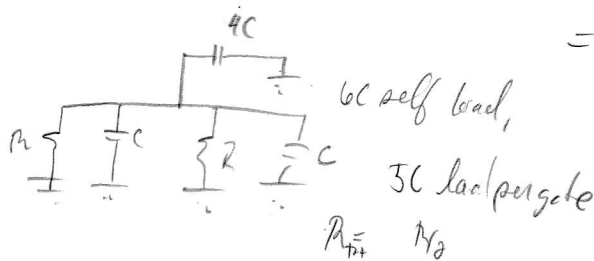
+ each gate input is  $4C + 7C = 5C$

$$t_{rise} = \frac{R}{2} \cdot 4C + R(6C + 5Ch)$$

$$= 2RC + 6RC + 5RCh$$

$$= 8RC + 5RCh = T_{rise}$$

Falling  $\Rightarrow$



$6C$  self load,

$5C$  load per gate

$R_{th} = R_D$

$$t_{fall} = \frac{R}{2}(6C + 5Ch)$$

$$T_{fall} = (3RC + \frac{5}{2}RCh)$$

2-4.11)(a)

$G = \Pi g_i$

NAND

NOR

$$G = (n+2)/3 \cdot 1 = (6+2)/3 \cdot 1 = 8/3 = G$$

$N=2$

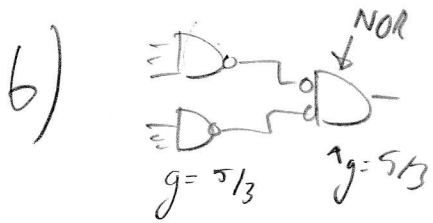
$$P = 6 \cdot 1 = 7$$

$$\Rightarrow D = N(GH)^{1/N}$$

$$H = \frac{1}{5} \quad \frac{5}{20}$$

$$D = \frac{10.27}{14.30} \quad \frac{21.61}{21.61}$$

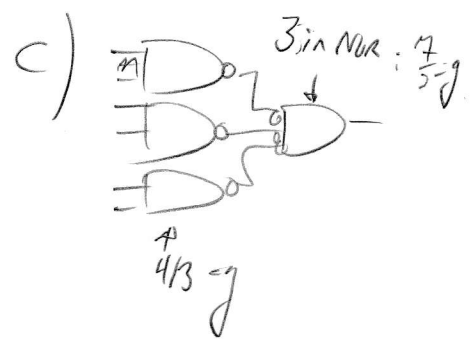




$$G = \frac{5}{3} \cdot \frac{5}{3} = \frac{25}{9} = 6$$

$$P = 3 + 2 = 5 \quad N = 2$$

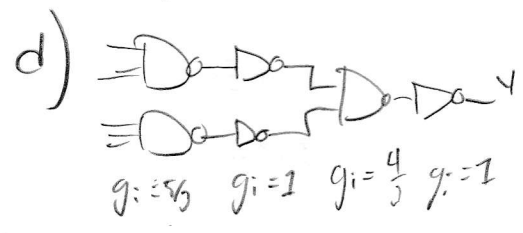
H =	1	5	20
D =	8.33	12.45	19.91



$$mg = \frac{7}{5} \cdot \frac{4}{3} = \frac{28}{9} = 6$$

$$P = 2 \times 3, \quad N = 2$$

H =	1	5	20
D =	8.52	12.89	20.78



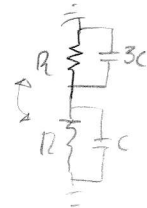
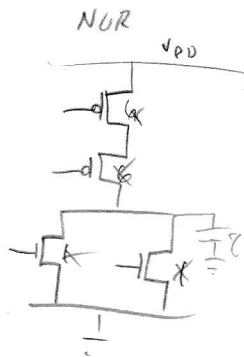
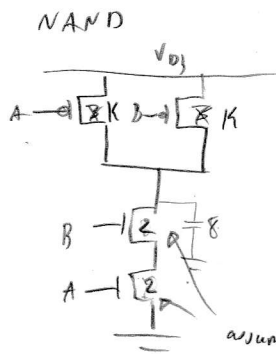
$$mg_i = \frac{5}{3} \cdot 1 \cdot \frac{4}{3} \cdot 1 = \frac{20}{9}$$

$$P = 3 + 1 + 2 + 1 = 7, \quad N = 2$$

H=1	5	20
D= 9.98	13.67	20.33

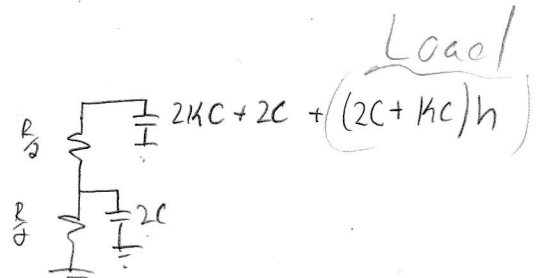
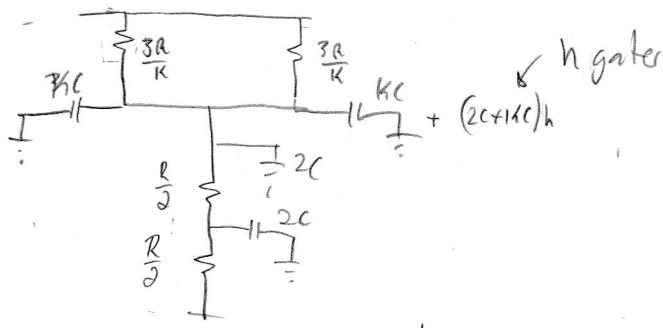
Design B is better for  $H=1$  &  $H=5$  as it has the lowest logical effort, design d is best for  $H=20$  as it has the lowest logical effort (probably due to long path allowing load to be spread/gradually increased)

3-4.15

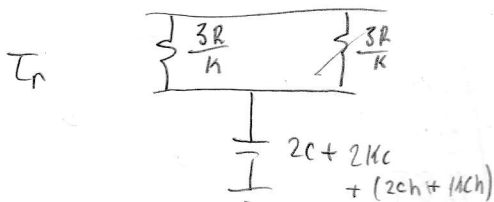


$$t_{fall} = \text{delay rise} = \frac{4RC + 4RCh}{1}$$

$$d = gh + p = \frac{C_{out}}{C_{in}g} + p$$



$$t_{d, \text{No Load}} = \frac{R}{2} 2C + R(2Kc + 2C) = RC + 2RC/K + 2RC = 3RC + 2RC/K$$



$$t_{d, \text{No Load}} = \frac{3R}{K} (2C + 2Kc) = \frac{6RC}{K} + 6RC$$

$$t_F = t_r \left( \frac{6RC}{K} + 6RC \right) = (3RC + 2RC/K)^{1/2}$$

$$\Rightarrow 6RC + 6RC \cdot K = 3RC \cdot K + 2RC/K^2$$

$$\Rightarrow 0 = 2RC/K^2 - 3RC \cdot K - 6RC$$

$$0 = K^2 - \frac{3}{2}K - 3$$

$$\Rightarrow K = 2.04 \text{ for equal delay}$$

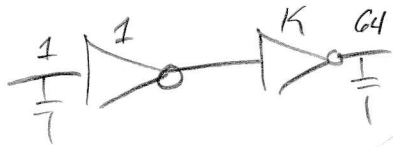
$$\begin{aligned} \text{delay w/ load} = t &= 3RC + 2RC \cdot 2.04 + (2C + \frac{2.04}{K}c)h \\ &= (8.28 + 4.64h)RC \\ \text{min } t_0 &= 4RC + 4RCh \end{aligned}$$

$$P = 2.04, \quad g = 1.16$$

4- 5.5)

Minimum number of gates will consume least energy, or minimal capacitance will be created with min. gates,

so for a buffer this is 2 inverters = minimum



$$g\left(\frac{C_{out}}{C_{in}}\right)$$

effort

$$20 = d = gh + p = \left(K + \frac{G4}{K}\right) + 2 \times P$$

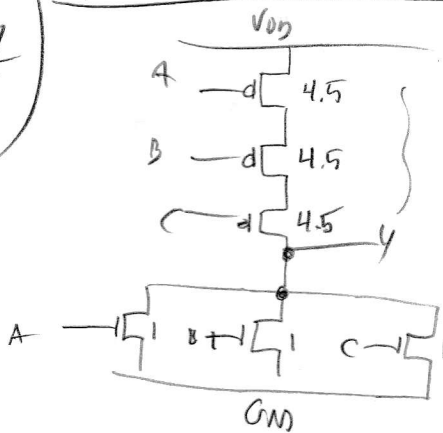
$$\Rightarrow 0 = K + \frac{64}{K} - 18 \Rightarrow 0 = K^2 - 18K + 64$$

$$K = 4.88 \text{ second}$$

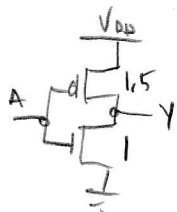
1 + first unit size

5- 9.7

P: L=50nm V=1.1 T=110C



comb w= 15



$$P_i = 2.85 \text{ ps (no load)}$$

$$d = t_d = p_i + gh$$

$$4.7158 = 2.85 + g \cdot 1$$

$$g_i = 1.8658$$

CONCLUSION:

Average  $G = 2.421$  close to ideal  $\frac{4}{3}$

Average  $P = 3.69$  close to ideal 3

individual P/E

FROM HSPICE SIM

INPUT	G	P
A	2.895	4.19
B	2.519	4.19
C	1.85	2.69
Average	2.421	3.69

FROM BOOK

$$\text{Ideal } G = \frac{4}{3} = 2.33$$

$$\text{Ideal } P = 3$$

$$\text{in A: } \tau_p \text{ unloaded} = 11.94 \text{ ps UNLOADED}$$

$$\tau_{p0A} = 17.343 \text{ ps LOADED w/ 1 gate}$$

$$\rightarrow d = \tau_p = 11.94 \text{ ps} + 5.403 \text{ h}$$

$$P = \frac{11.94}{2.85} = 4.19 = P_A, \frac{5.403}{1.8658} = 2.895 = G_A$$

$$\text{IN B: } \tau_p \text{ unloads} = 11.95 \text{ ps}$$

$$\tau_p \text{ loaded} = 16.65 \text{ ps (1 gate)}$$

$$d = \tau_p = 11.95 + 4.7 \text{ h}$$

$$P = \frac{11.95}{2.85} = 4.19 = P_B, \frac{4.7}{1.8658} = 2.519 = G_B$$

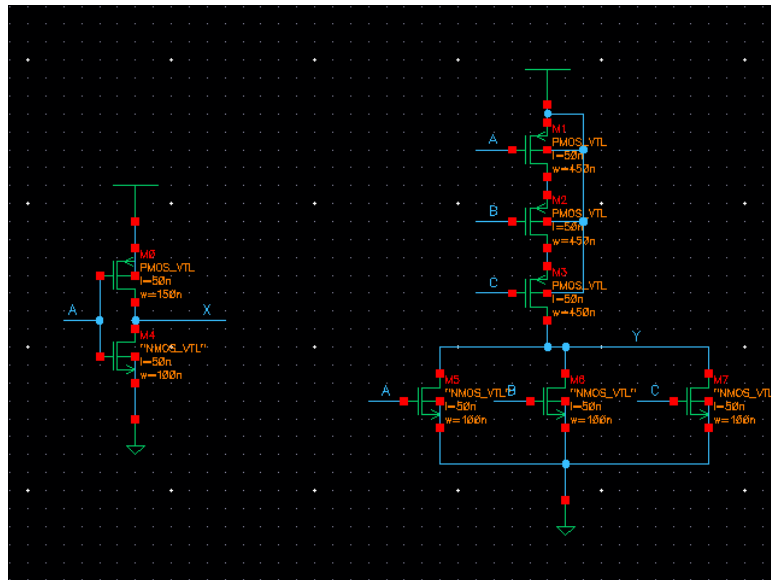
$$\text{INC: } \tau_p \text{ unloaded} = 7.69 \text{ ps}$$

$$\tau_p \text{ loaded (1 gate)} = 11.15 \text{ ps}$$

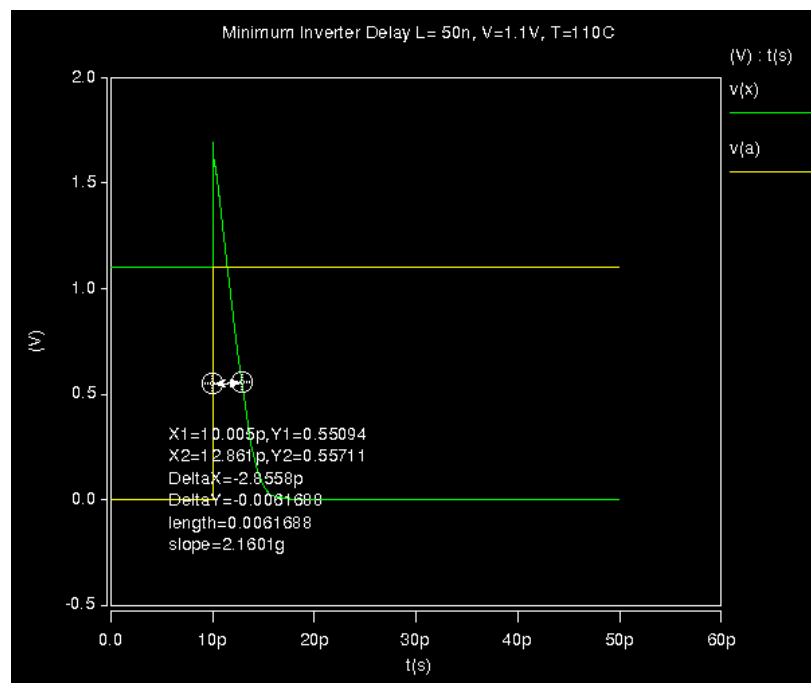
$$d = \tau_p = 7.69 + 3.46 \text{ h} \Rightarrow P_C = 2.69 \text{ } G_C = 1.89$$

### Problem 9.7)

To find the logical effort of a 3 IN NOR in FreePDK45, I made a HSPICE simulation with a minimal inverter where  $L=50\text{nm}$  and  $W=100\text{nm}$  for the NMOS and  $W=150\text{nm}$  for the PMOS. I also made a 3 in NOR gate that maintained the same overall ration of P width to Nwidth. This is shown below

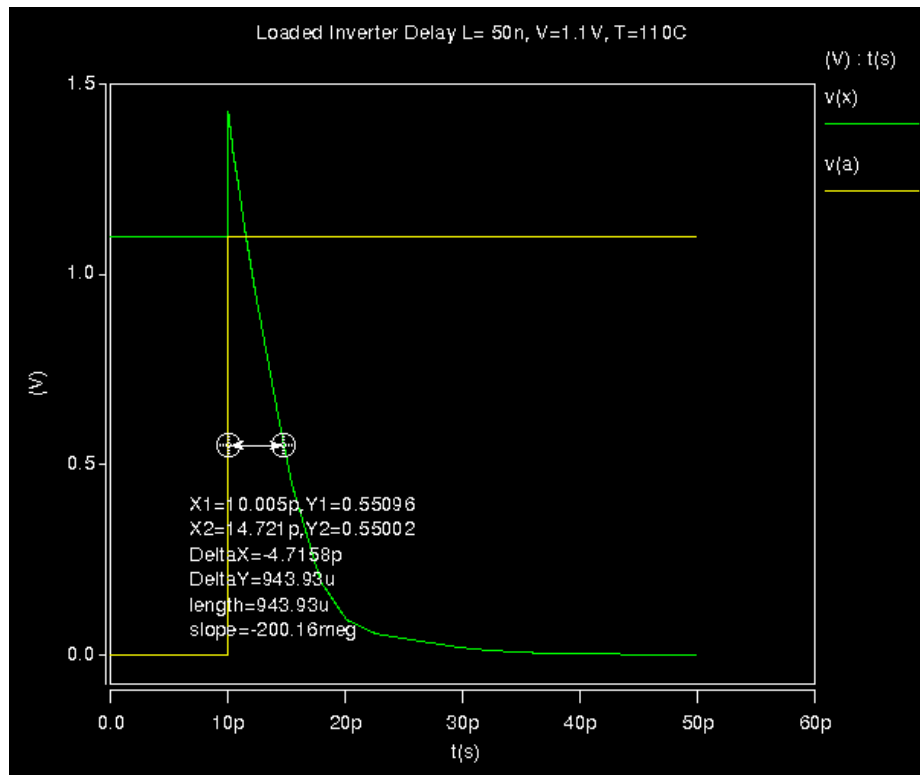


I then ran a simulation of the inverter (no loading) with  $T=110\text{C}$  and  $V_{dd}=1.1\text{V}$  to determine the minimal (intrinsic delay) for this process.

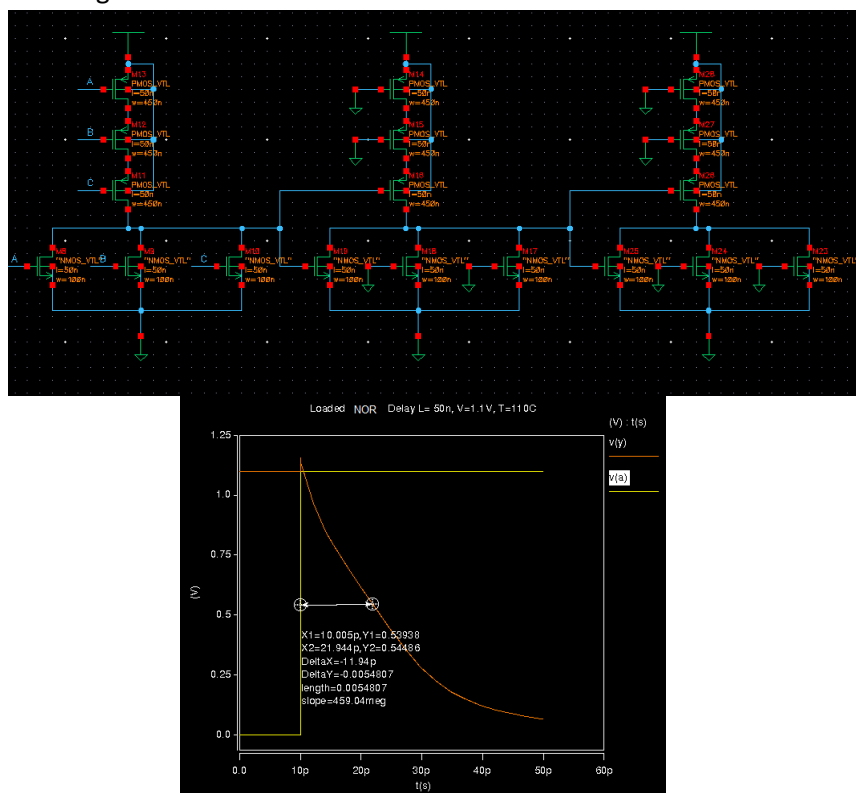


Doing this shows that the minimal propagation delay  $tp0$  is  $2.856\text{ps}$

I ran another simulation with this gate loaded with a single inverter, shown below. The loaded delay is  $4.72\text{ps}$ , therefore we can say the delay for this inverter with  $h$  gates loading it is  $tp = 2.85 + h \cdot (4.72 - 2.85) = 2.85 + 1.87 \cdot h$



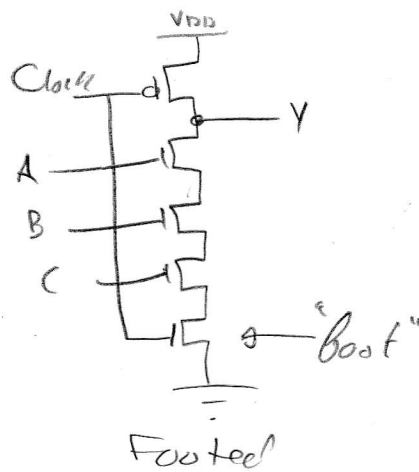
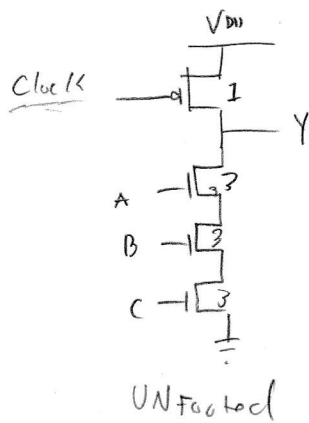
The NOR gate was then simulated with no load on the output and a step was applied separately to each input to determine the unloaded delay for each input. The NOR gate was then loaded with a chain of NOR gates as shown below to determine the propagation delay for a single 3IN NOR load. From this a delay equation was derived for each input (on handwritten parts of assignment). The values for logical effort in terms of P and G were then found by dividing the p and g values for each input of the NOR by the minimal inverter p and g values. The found P and G values are listed on the handwritten part of this assignment



Above: example simulation of NOR delay for unloaded NOR gate and input A tested. I'm not going to show graphics of all the sims as it is redundant/waste of space. The measured values are given on the handwritten part of this problem

6 - 9.27)

# NAND



# NOR

